Article

Carrier-resolved photo-Hall effect

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Published online: 7 October 2019	The fundamental parameters of majority and minority charge carriers—including their type, density and mobility—govern the performance of semiconductor devices yet can be difficult to measure. Although the Hall measurement technique is currently the standard for extracting the properties of majority carriers, those of minority carriers have typically only been accessible through the application of separate

[...]

The Hall effect measurement is one of the most important characterization techniques for electronic materials, and the effect has become the basis of fundamental advances in condensed matter physics, such as the integer and fractional quantum Hall effects^{4,5}. The measurements reveal fundamental information about the majority charge carrier—that is, its type (p or n), density and mobility. In a solar cell, the parameters of the majority carrier determine the overall device architecture, the width of the depletion region and the bulk series resistance. The properties of the minority carrier, however, determine other key parameters that directly affect the overall performance of the device, such as recombination lifetime (τ), diffusion length (L_D) and recombination coefficients (k_n). Unfortunately, the standard Hall measurement yields information regarding only the majority carrier. Attempts to measure the properties of both majority and minority carriers in high-performance

A full understanding of the charge-transport properties of perovskites will help to elucidate the operating principles of devices that contain these materials, thereby guiding their further improvement.

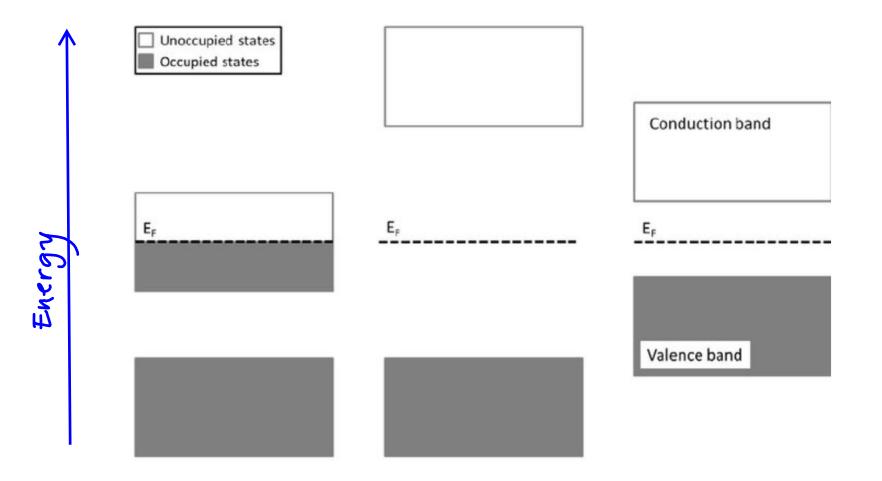
nature

In this work we present a carrier-resolved photo-Hall (CRPH) measurement technique that is capable of simultaneously extracting the mobilities, densities and subsequent derivative parameters (τ , $L_{\rm D}$) of both majority and minority carriers as a function of light intensity. This technique relies on two key elements: an equation that yields the difference between the Hall mobilities of the hole and electron, and a high-sensitivity Hall measurement using a parallel dipole line (PDL) a.c. Hall system¹⁸ (Fig. 1a, b). In the classic Hall measurement without illumination, three parameters can be obtained for majority carriers: the type (p or n), from the sign of Hall coefficient *H*; the carrier density ($n_{\rm c}$ =r/He); and the Hall mobility ($\mu_{\rm H}$ =oH); where e is the electron charge

Electronic Band Structure

· Kittel · Simon · Singleton

Goal

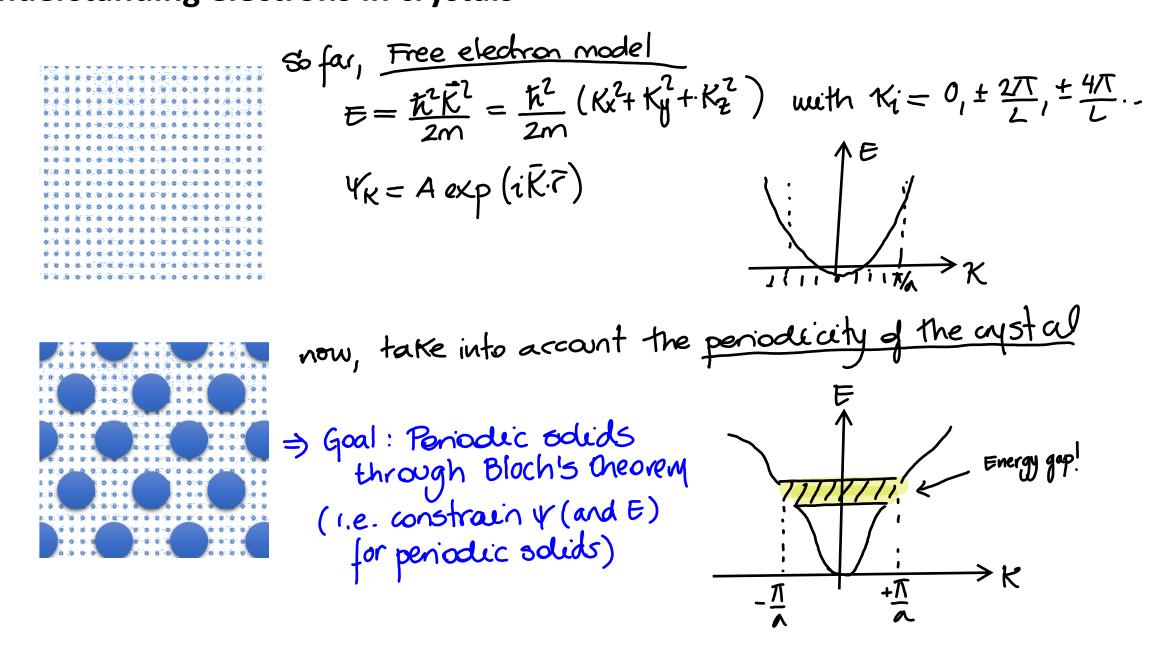


Free e-model works for some physical properties tout leaves many open questions

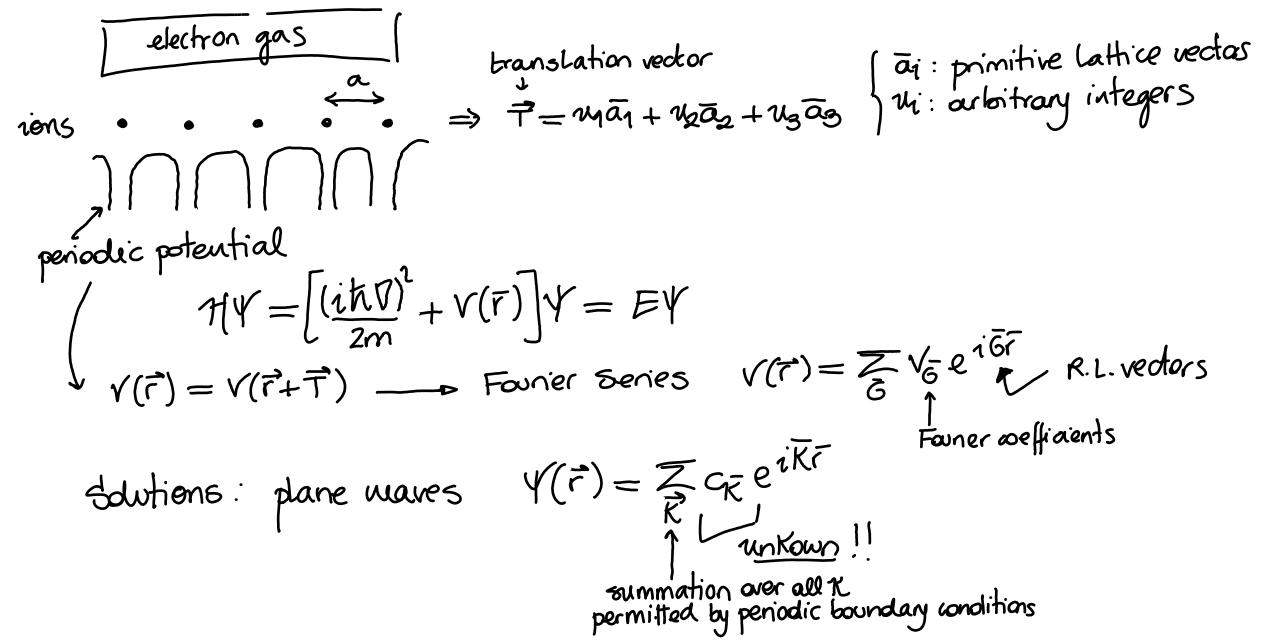
* difference between metal/insulator/semiconductor? * Scattering length lv NF. Z~ 100 g at RT - why do e- not scatter from nuclei? * Hall effect in why orign seems to indicate positive changes? * Hall effect in why # conduction e- is not always = # valence e-? * Heat capacity $\frac{mth}{m} = \frac{T(observed)}{T(calculated)} \neq 1?$ Cel = T

Bloch theorem

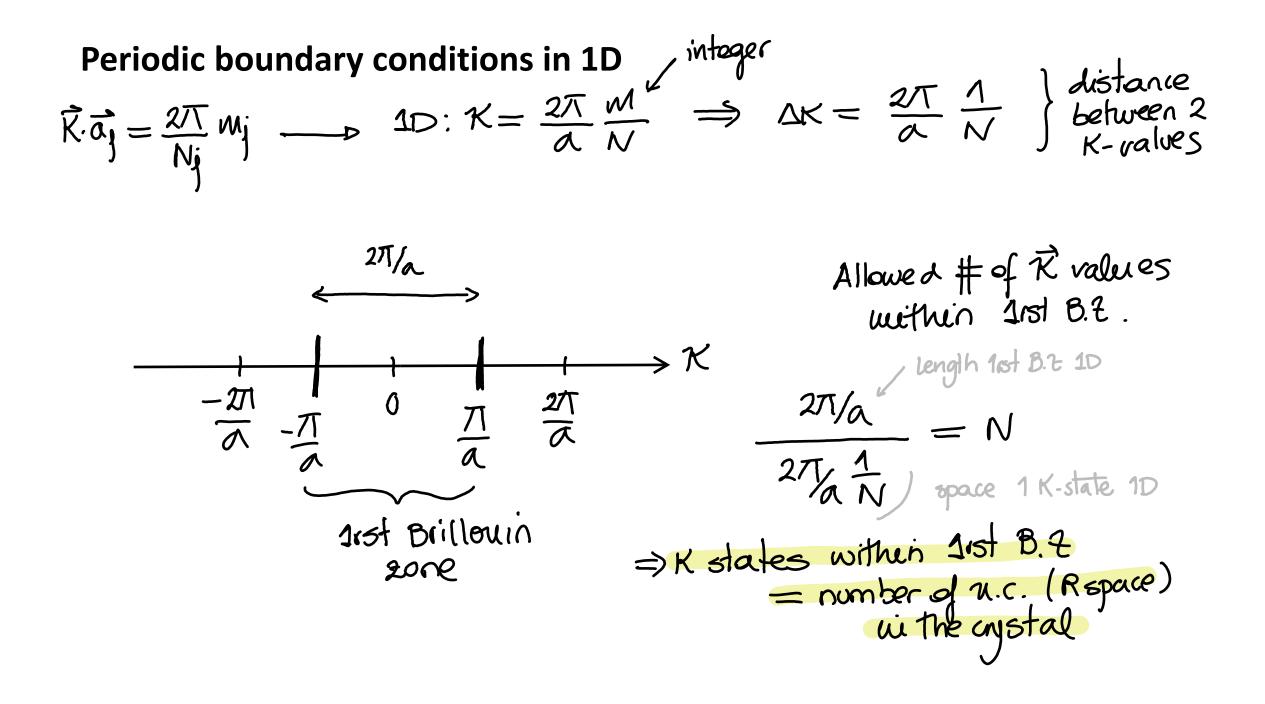
Understanding electrons in crystals



Schrödinger equation



Born-von Karman conditions
$$\longrightarrow$$
 restrictions on the possible \overline{K} values
(spenodic boundary conditions)
Nj: # d u.c. along direction \overline{a}_{j} ($j = 1, 2, 3$)
NjN2Ng = N = # d u.c in the crystal
NNN2Ng = N = # d u.c in the crystal
Periodic Boundary (ond. $\Psi(\overline{r} + N_{j}\overline{a}_{j}) = \Psi(\overline{r})$
 $\Psi(\overline{r} + N_{j}\overline{a}_{j}) = \overline{K} c_{\overline{k}} e^{i\overline{k}(\overline{r} + N_{j}\overline{a}_{j})} = \Psi(\overline{r}) \cdot e^{i\overline{k}\cdot N_{j}\overline{a}_{j}}$
 $\Psi(\overline{r} + N_{j}\overline{a}_{j}) = \overline{K} c_{\overline{k}} e^{i\overline{k}(\overline{r} + N_{j}\overline{a}_{j})} = \Psi(\overline{r}) \cdot e^{i\overline{k}\cdot N_{j}\overline{a}_{j}}$
 $\overline{K} can only take discrete values!$



Periodic boundary conditions in 3D

$$\vec{k} = \vec{j} \cdot \vec{k} \cdot \vec{k} \quad \text{primitive reciprocal lattice vector}$$

$$\vec{k} \cdot \vec{a}_{j} = \vec{j} \cdot \vec{k} \cdot \vec{k} \quad \text{primitive reciprocal lattice vector}$$

$$\vec{k} \cdot \vec{a}_{j} = \vec{j} \cdot \vec{k} \cdot \vec{k} \quad \vec{k} \cdot \vec{k} \quad \vec$$

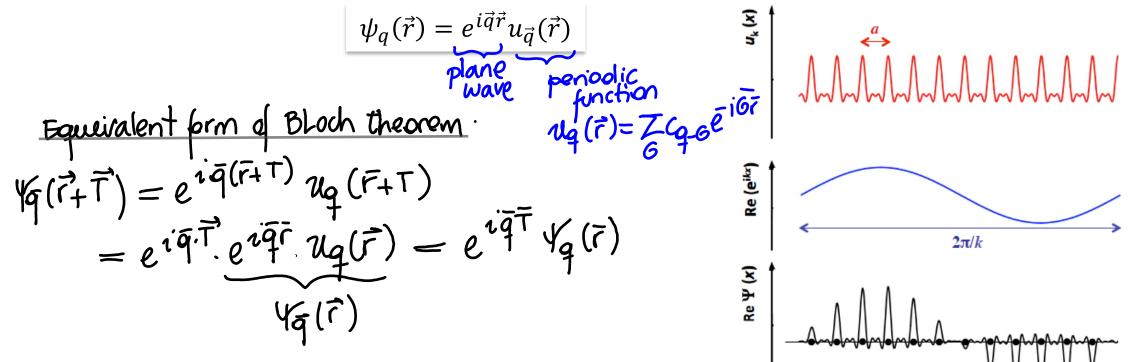
Eigenstates of Schrödinger equation in a periodic potential

let's deal with solutions within Irst B.Z. $\vec{K} = \vec{q} - \vec{G}$, $\int \vec{q}$: vector within 1rst B.2 \vec{G} : R.L. vector $\left(\frac{\hbar^{2}(\bar{q}-\bar{G}')^{2}}{2m}-E\right)_{q-d}+\frac{7}{6}V_{\bar{G}}_{\bar{G}}_{\bar{q}}_{\bar{G}}$ $G+G'\equiv G"$ $\left(\frac{\hbar^2(\mathbf{q}-\mathbf{G}')^2}{2m}-\mathbf{F}\right)\mathbf{G}_{\mathbf{q}}-\mathbf{\bar{G}}'+\mathbf{\bar{G}}_{\mathbf{\bar{G}}}^{\mathbf{T}}\mathbf{V}_{\mathbf{\bar{G}}}\mathbf{L}\mathbf{G}^{\mathbf{T}}\mathbf{G}_{\mathbf{\bar{q}}}-\mathbf{G}^{\mathbf{T}}=\mathbf{O}$ 6'-) G $\int \left(\frac{\hbar^2(\bar{q}-\bar{6})^2}{2m} + F\right) c_{\bar{q}} - \bar{6} + \frac{1}{\bar{6}} \sqrt{\bar{6}} - \bar{6} c_{\bar{q}} - \bar{6} = 0$ $\Rightarrow V_{q}(\vec{r}) = Z_{q} = \bar{e}^{i(\bar{q}-\bar{e})\cdot\bar{r}} = e^{i\bar{q}\bar{r}} Z_{q} = e^{i\bar{e}\bar{r}}$ ug(r) Function which has the ug(r) perioducity of the lattice.

Bloch's theorem

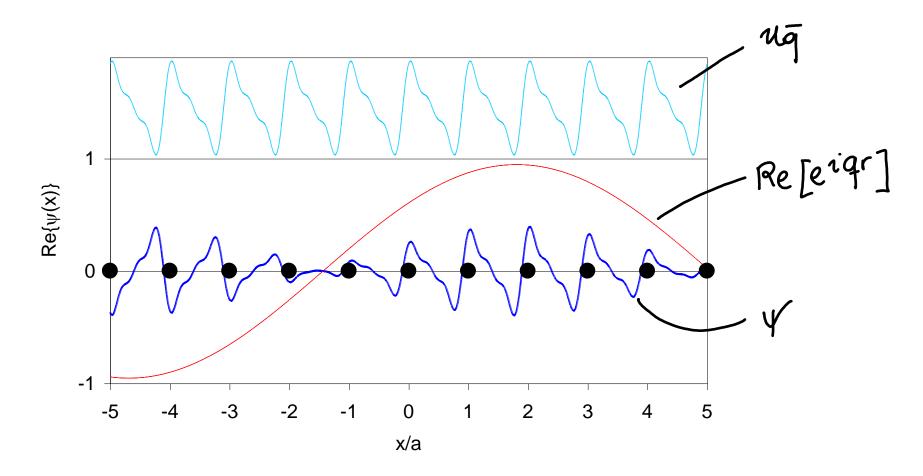
If plays a very important role ni electronic band stucture theory.

The eigenstates ψ of a one-electron Hamiltonian $H = \frac{\hbar^2 \nabla^2}{2m} + V(\vec{r})$, where $V(\vec{r} + \vec{T}) = V(\vec{r})$ for all Bravais lattice translation vector \vec{T} , can be chosen to be a planar wave times a function with the periodicity of the Bravais lattice.

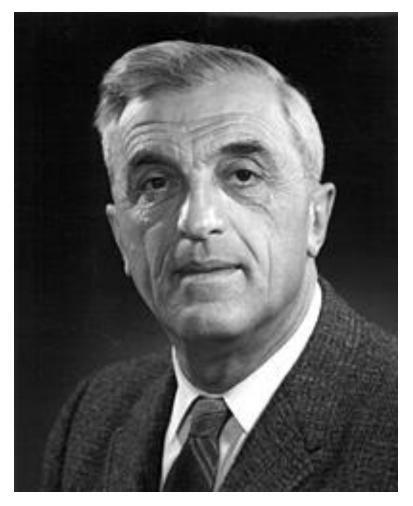


- True for any particle propagating in a lattice
- No assumptions made about the potential *strength*

$$\psi_q(\vec{r}) = e^{i\vec{q}\vec{r}} u_{j,\vec{q}}$$



Felix Bloch



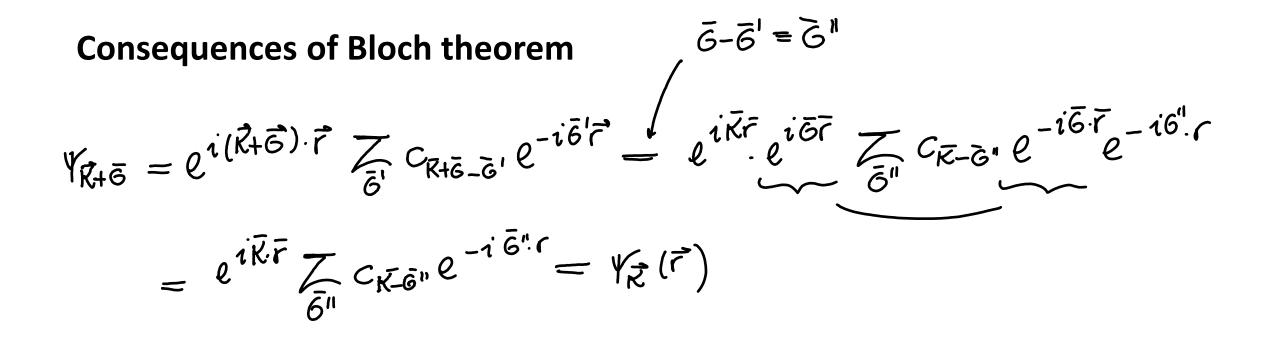
when I started to think about it, I felt that the main problem was to explain how the electrons could sneak by all the ions in a metal....

By straight Fourier analysis I found to my delight that the wave differed from the plane wave of free electrons only by a periodic modulation'

F. BLOCH

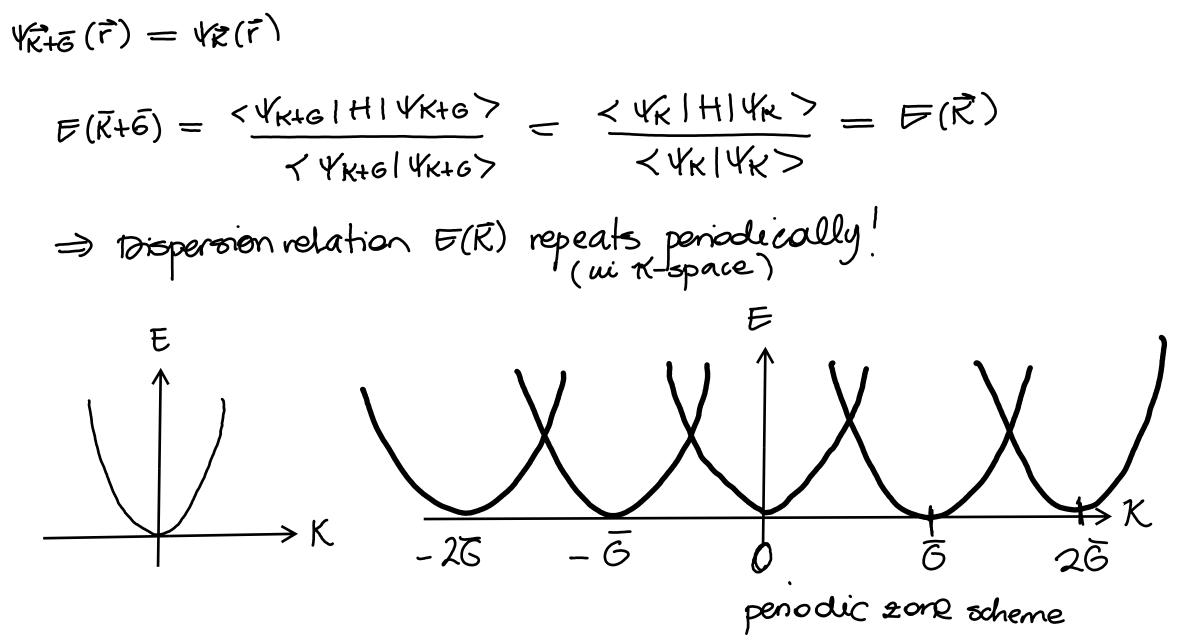
Born in Zurich (1905)

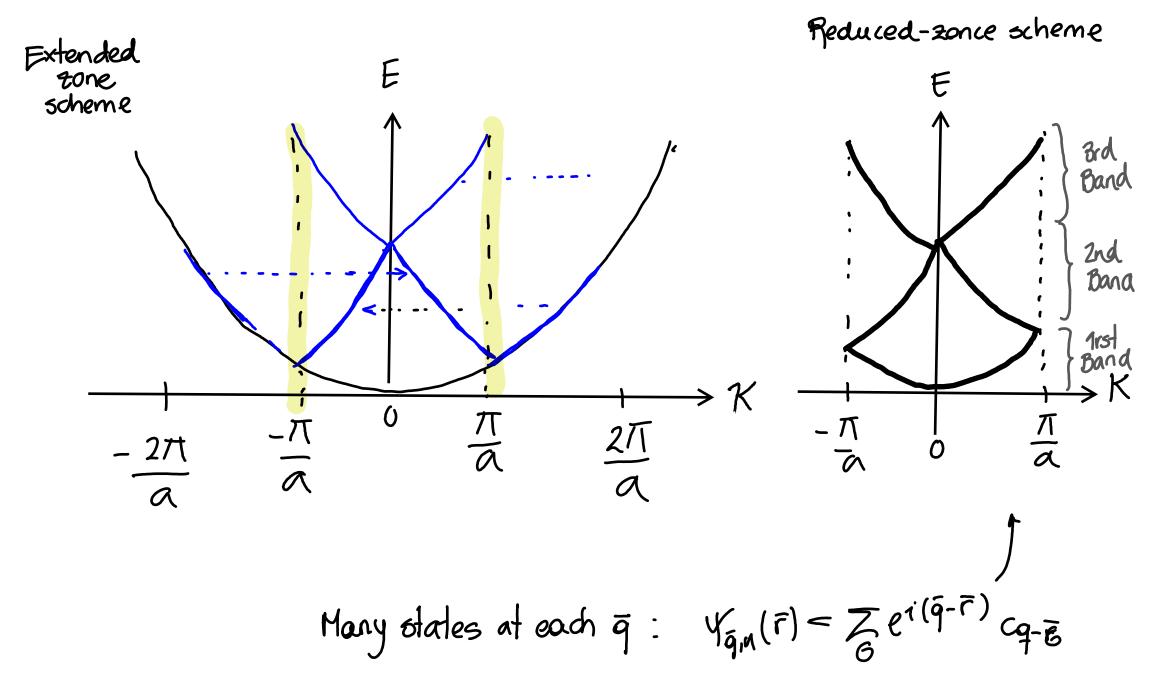
Awarded 1952 Nobel Prize for Physics First director of CERN



2 Bloch functions mith quantum numbers R differeing by a R.L. vector are identical

Consequences of Bloch theorem





Nearly free electron model

